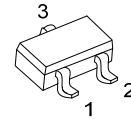
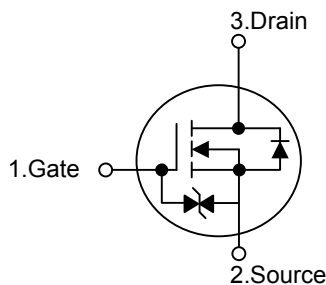


**UK3019****Power MOSFET****2.5V DRIVE SILICON
N-CHANNEL MOSFET****DESCRIPTION**

The UTC **UK3019** is a silicon N-channel MOSFET which has been designed to minimize on-state resistance while it provides rugged, reliable and fast switching performance. The product is particularly suited for low voltage, low current applications such as small servo motor controller, power MOSFET gate drivers, and other switching applications.

FEATURES

- * Min $V_{DS} = 30V$
- * $R_{DS(ON)} \leq 8.0\Omega$ @ $I_D = 10mA$, $V_{GS} = 4.0V$
- * $R_{DS(ON)} \leq 13\Omega$ @ $I_D = 1mA$, $V_{GS} = 2.5V$
- * Pulsed $I_D = 400mA$
- * Low Voltage Drive (2.5V)

SYMBOL

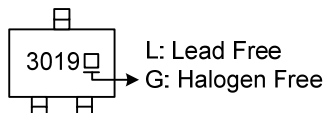
SOT-23-3
(JEDEC TO-236)

ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UK3019L-AE2-R	UK3019G-AE2-R	SOT-23-3	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

UK3019G-AE2-R		
(1)Packing Type	(1) R: Tape Reel	
(2)Package Type	(2) AE2: SOT-23-3	
(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free	

MARKING

■ **ABSOLUTE MAXIMUM RATING** ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	Continuous	I_D	100	mA
	Pulsed (Note 2)	I_{DP}	400	mA
Power Dissipation (Note 3)		P_D	200	mW
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 50\%$

3. With each pin mounted on the recommended lands.

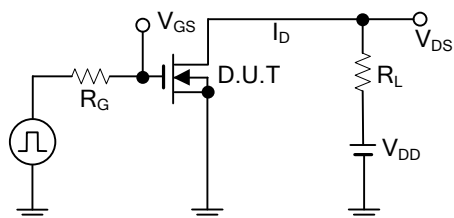
■ **THERMAL CHARACTERISTICS**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	625	$^{\circ}\text{C/W}$

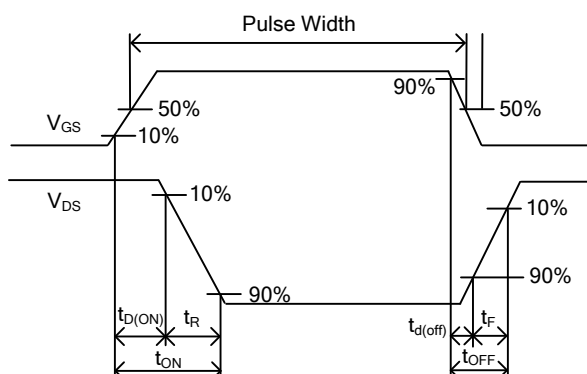
■ **ELECTRICAL CHARACTERISTICS** ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =10μA	30			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±1	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =3V, I _D =100μA	0.8		1.5	V
Static drain-source on-state resistance	R _{DS(ON)}	I _D =10mA, V _{GS} =4.0V		5.0	8.0	Ω
		I _D =1mA, V _{GS} =2.5V		7.0	13	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} =5V, V _{GS} =0V, f = 1MHz		13		pF
Output Capacitance	C _{OSS}			9		pF
Reverse Transfer Capacitance	C _{RSS}			4		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	t _{D(ON)}	V _{GS} =5V, V _{DD} ≈5V I _D =10mA, R _L =500Ω, R _G =10Ω		15		ns
Turn-ON Rise Time	t _R			35		ns
Turn-OFF Delay Time	t _{D(OFF)}			80		ns
Turn-OFF Fall-Time	t _F			80		ns

■ TEST CIRCUITS AND WAVEFORMS



Switching Time Measurement Circuit



Switching Time Waveforms

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